

Form PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Attorney Docket No. 5308-395		Serial No. <u>10/790406</u> To be assigned	
LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)				Applicant: O'Loughlin et al.		Filing Date: Concurrently herewith	
				GAU: Unknown			
<b>U.S. PATENT DOCUMENTS</b>							
Examiner Initials	Document No.	Date (m/d/y)	Name	Class	Subclass	Filing Date if Appropriate	
JO	1	US2003/0079689A1	5/1/03	Sumakeris et al.	118	725	
<b>FOREIGN PATENT DOCUMENTS</b>							
	Document Number	Date	Country	Class	Subclass	Translation (Yes/No)	
<b>OTHER DOCUMENTS</b>							
JO	2	Okada et al. "Crystallographic defects under surface morphological defects of 4H-SiC homoepitaxial films," ICSCRM 2003 Poster Sessions.					
JO	3	Wahab et al. "Influence of epitaxial growth and substrate-induced defects on the breakdown of 4H-SiC Schottky diodes," <i>Applied Physics Letters</i> , Vol. 76, No. 19, May 8, 2000, pp. 2725-7.					
JO	4	U.S. Application Serial No. 10/414,787 entitled <i>Methods and Apparatus for Controlling Formation of Deposits in a Deposition System and Depositions Systems and Methods Including the Same</i> , filed April 16, 2003.					
JO	5	U.S. Application Serial No. 09/756,548, titled <i>Gas Driven Rotation Apparatus and Method for Forming Silicon Carbide Layers</i> , filed January 8, 2001.					
JO	6	U.S. Application Serial No. 10/117,858, titled <i>Gas Driven Planetary Rotation Apparatus and Methods for Forming Silicon Carbide Layers</i> , filed April 8, 2002.					

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Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.